Unit: mm

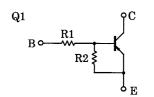
TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process) Silicon NPN Epitaxial Type (PCT Process)

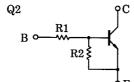
RN4903

Switching, Inverter Circuit, Interface Circuit And Driver Circuit Applications

- Includeing two devices in US6 (ultra super mini type with 6 leads)
- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process

Equivalent Circuit and Bias Resister Values





R1: 22kΩ R2: 22kΩ (Q1, Q2 Common)

Q1 Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-50	V
Collector-emitter voltage	V_{CEO}	-50	V
Emitter-base voltage	V _{EBO}	-10	V
Collector current	IC	-100	mA

2.1 ± 0.1 1.25 ± 0.1 $0 \sim 0.1$ EMITTER 1 (E1) BASE 1 (B1) COLLECTOR 2 (C2)EMITTER 2 (E2) BASE 2 (B2) US6 COLLECTOR 1 (C1)**JEDEC EIAJ TOSHIBA** 2-2J1A

Weight: 6.8mg

Q2 Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	50	V
Collector-emitter voltage	V _{CEO}	50	V
Emitter-base voltage	V _{EBO}	10	V
Collector current	Ic	100	mA

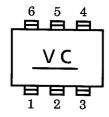
1

Q1, Q2 Common Maximum Ratings (Ta = 25°C)

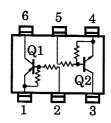
Characteristic	Symbol	Rating	Unit
Collector power dissipation	P _C *	200	mW
Junction temperature	T _j 150		°C
Storage temperature range	T _{stg}	-55~150	°C

^{*} Total rating

Marking



Equivalent Circuit (Top View)



Q1 Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	_	$V_{CB} = -50V$, $I_E = 0$	_	-	-100	nA
	I _{CEO}	_	V _{CE} = -50V, I _B = 0	_	_	-500	ПА
Emitter cut-off current	I _{EBO}	_	V _{EB} = −10V, I _C = 0	-0.17	_	-0.33	mA
DC current gain	h _{FE}	_	V _{CE} = −5V, I _C = −10mA	70	_	_	_
Collector-emitter saturation voltage	V _{CE (sat)}	_	I _C = -5mA, I _B = -0.25mA	_	-0.1	-0.3	V
Input voltage (ON)	V _{I (ON)}	_	$V_{CE} = -0.2V, I_{C} = -5mA$	-1.3	_	-3.0	V
Input voltage (OFF)	V _{I (OFF)}	_	V _{CE} = -5V, I _C = -0.1mA	-1.0	_	-1.5	V
Transition frequency	f _T	_	$V_{CE} = -10V, I_{C} = -5mA$	_	200	_	MHz
Collector output capacitance	C _{ob}	_	V _{CB} = −10V, I _E = 0, f = 1MHz	_	3	6	pF

2

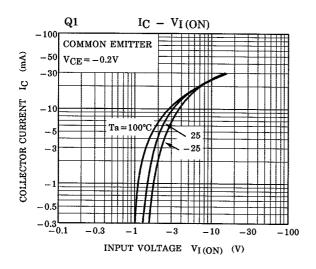
Q2 Electrical Characteristics (Ta = 25°C)

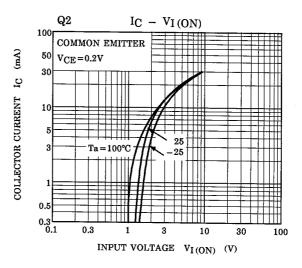
Characteristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	_	V _{CB} = 50V, I _E = 0	_	_	100	nA
	I _{CEO}	_	V _{CE} = 50V, I _B = 0	_	_	500	
Emitter cut-off current	I _{EBO}	_	V _{EB} = 10V, I _C = 0	0.17	_	0.33	mA
DC current gain	h _{FE}	_	V _{CE} = 5V, I _C = 10mA	70	_	_	_
Collector-emitter saturation voltage	V _{CE} (sat)	_	I _C = 5mA, I _B = 0.25mA	_	0.1	0.3	V
Input voltage (ON)	V _{I (ON)}	_	V _{CE} = 0.2V, I _C = 5mA	1.3	_	3.0	V
Input voltage (OFF)	V _{I (OFF)}	_	V _{CE} = 5V, I _C = 0.1mA	1.0	_	1.5	٧
Transition frequency	f _T	_	V _{CE} = 10V, I _C = 5mA	_	250	_	MHz
Collector output capacitance	C _{ob}	_	V _{CB} = 10V, I _E = 0, f = 1 MHz	_	3	6	pF

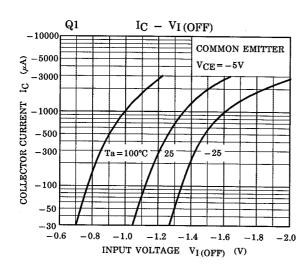
Q1, Q2 Common Electrical Characteristics (Ta = 25°C)

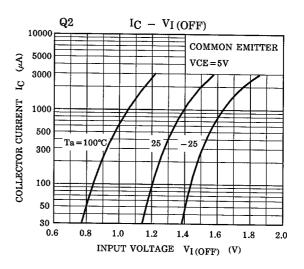
Characteristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Input resistor	R1	_	_	15.4	22	28.6	kΩ
Resistor ratio	R1/R2	_	I	0.9	1.0	1.1	_

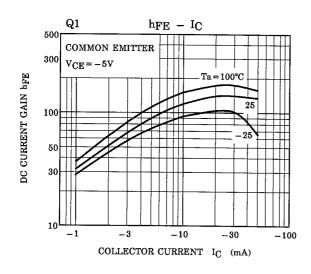
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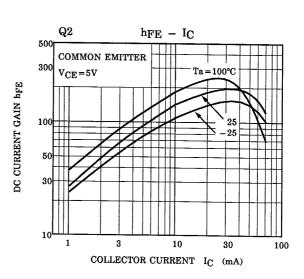












4

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